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(71) Applicant (for all designated States except US): **KONINKLIJKE PHILIPS ELECTRONICS N.V.** [NL/NL];
Groenewoudseweg 1, NL-5621 BA Eindhoven (NL).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **HUETING, Raymond, J., E.** [NL/NL]; c/o Philips Intellectual Property,

& Standards, Cross Oak Lane, Redhill Surrey RH1 5HA (GB). **HLJZEN, Erwin, A.** [NL/BE]; c/o Philips Intellectual Property, & Standards, Cross Oak Lane, Redhill Surrey RH1 5HA (GB).

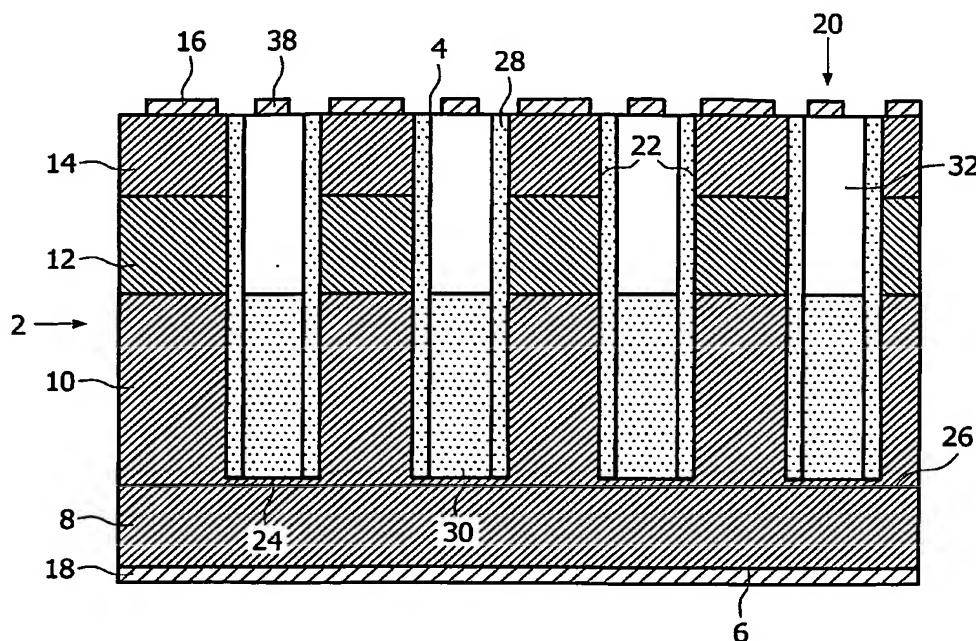
(74) Agents: **WILLIAMSON, Paul, L.** et al.; c/o Philips Intellectual Property, & Standards, Cross Oak Lane, Redhill Surrey RH1 5HA (GB).

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(54) Title: TRENCH MOSFET



(57) Abstract: The invention relates to a trench MOSFET with drain (8), drift region (10) body (12) and source (14). In order to improve the figure of merit for use of the MOSFET as control and sync FETs, the trench (20) is partially filled with dielectric (24) adjacent to the drift region (10) and a graded doping profile is used in the drift region (10).

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